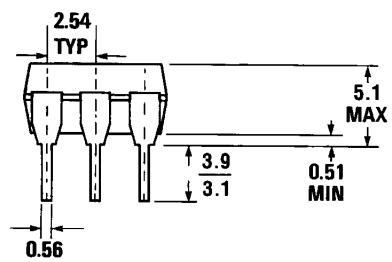
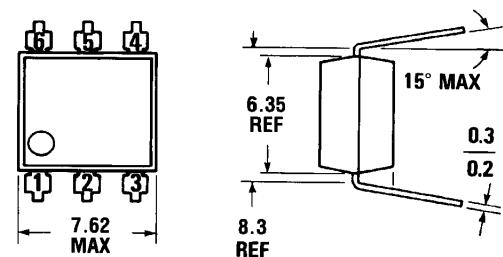




AC INPUT/PHOTOTRANSISTOR OPTOCOUPLES

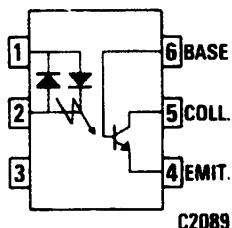
H11AA1 H11AA3
H11AA2 H11AA4

PACKAGE DIMENSIONS



DIMENSIONS IN mm
PACKAGE CODE E

ST1603-02



Equivalent Circuit

DESCRIPTION

The H11AAX family of devices has two GaAs emitters connected in inverse parallel driving a single silicon phototransistor output.

FEATURES

- Bi-polar emitter input
- Built-in reverse polarity input protection
- UL recognized (File #E90700)

APPLICATIONS

- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface

ABSOLUTE MAXIMUM RATINGS

TOTAL PACKAGE

Power dissipation	350 mW
Derate linearly from 25°C	4.6 mW
Storage temperature	-55°C to 150°C
Operating temperature	-55°C to 100°C
Lead temperature (soldering, 10 sec)	260°C

INPUT DIODE

Forward current	100 mA
Peak forward current (1 μs pulse, 300 pps)	±1.0 A
Power dissipation	200 mW
Derate linearly from 25°C	2.6 mW/°C

OUTPUT TRANSISTOR

Power dissipation	300 mW
Derate linearly from 25°C	4.0 mW/°C



AC INPUT/PHOTOTRANSISTOR OPTOCOUPERS

INDIVIDUAL COMPONENT CHARACTERISTICS ($T_A=25^\circ C$ Unless Otherwise Specified)

CHARACTERISTIC	SYMBOL	DEVICE	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE							
Forward voltage	V_F	ALL		1.2	1.5	V	$I_F = \pm 10 \text{ mA}$
Forward voltage coefficient	$\Delta V_F / \Delta T_A$	ALL		-1.9		mV/ $^\circ C$	$I_F = 2 \text{ mA}$
Junction capacitance	C_J	ALL		80		pF	$V_F = 0 \text{ V}, f = 1 \text{ MHz}$
OUTPUT TRANSISTOR							
Breakdown voltage Collector to emitter	BV_{CEO}	ALL	30			V	$I_C = 1 \text{ mA}, I_E = 0$
Collector to base	BV_{CBO}	ALL	70			V	$I_C = 100 \mu\text{A}, I_E = 0$
Emitter to base	BV_{EBO}	ALL	5			V	$I_E = 100 \mu\text{A}, I_C = 0$
Emitter to collector	BV_{ECO}	ALL	7			V	$I_E = 100 \mu\text{A}, I_C = 0$
Leakage current	I_{CEO}	H11AA1,3,4 H11AA2		50	nA		$V_{CE} = 10 \text{ V}, I_F = 0$
	I_{CEO}			200	nA		$V_{CE} = 10 \text{ V}, I_F = 0$
Capacitance							
Collector to emitter	C_{CE}	ALL		10		pF	$V_{CE} = 0, f = 1 \text{ MHz}$
Collector to base	C_{CB}	ALL		80		pF	$V_{CE} = 0, f = 1 \text{ MHz}$
Emitter to base	C_{EB}	ALL		15		pF	$V_{CE} = 0, f = 1 \text{ MHz}$

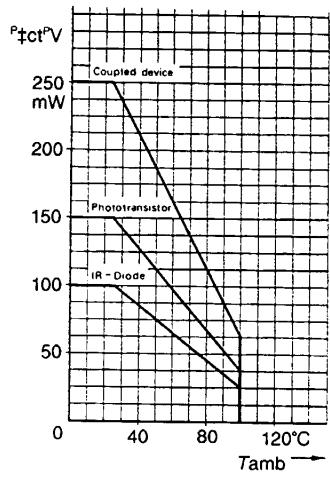
TRANSFER CHARACTERISTICS ($T_A=25^\circ C$ Unless Otherwise Specified)

CHARACTERISTIC	SYMBOL	DEVICE	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Current transfer (Collector-Emitter)	CTR_{CE}	H11AA4	100				$I_F = \pm 10 \text{ mA}, V_{CE} = 10 \text{ V}$
		H11AA3	50			%	$I_F = \pm 10 \text{ mA}, V_{CE} = 10 \text{ V}$
		H11AA1	20				$I_F = \pm 10 \text{ mA}, V_{CE} = 10 \text{ V}$
		H11AA2	10				$I_F = \pm 10 \text{ mA}, V_{CE} = 10 \text{ V}$
Current transfer ratio symmetry		ALL	0.33		3.0		$I_F = \pm 10 \text{ mA}, V_{CE} = 10 \text{ V}$ Fig. 6
Saturation voltage (Collector-Emitter)	V_{CESAT}	ALL		0.4		V	$I_F = \pm 10 \text{ mA}, I_{CE} = 0.5 \text{ mA}$
		H11AA3,4		0.4		V	$I_F = \pm 16 \text{ mA}, I_{CE} = 2.0 \text{ mA}$

ISOLATION CHARACTERISTICS ($T_A=25^\circ C$ Unless Otherwise Specified)

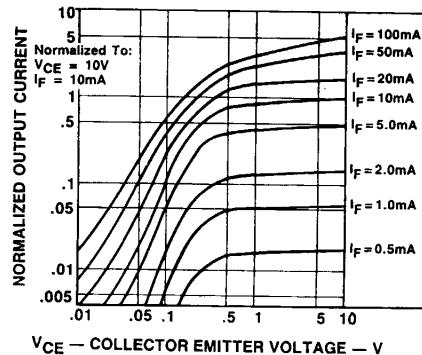
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Package capacitance input/output	C_{IO}		0.7		pF	$V_{IO} = 0, f = 1 \text{ MHz}$
Withstand insulation test voltage	V_{ISO}	5300			$V_{AC(RMS)}$	$I_{IO} \leq 1 \mu\text{A}, 1 \text{ minute}$
Insulation resistance	R_{ISO}	10^{11}			Ohms	$V_{IO} = 500 \text{ V}$

ELECTRICAL CHARACTERISTIC CURVES ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)



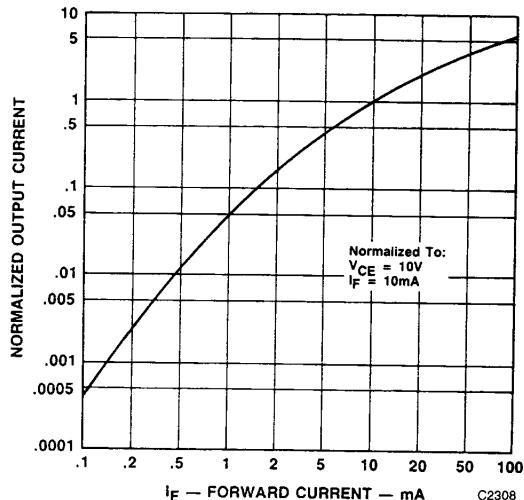
C2303

Fig. 1.



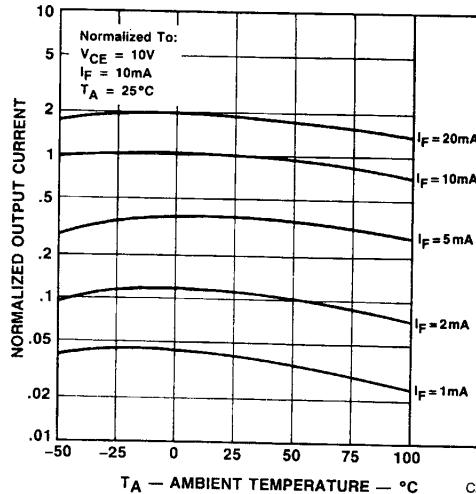
C2309

Fig. 2. Transfer Characteristics



C2308

Fig. 3. Input Current vs.
Output Current



C2305

Fig. 4. Output Current vs.
Temperature



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ELECTRICAL CHARACTERISTIC CURVES ($T_A=25^\circ\text{C}$ Unless Otherwise Specified) (Cont'd)

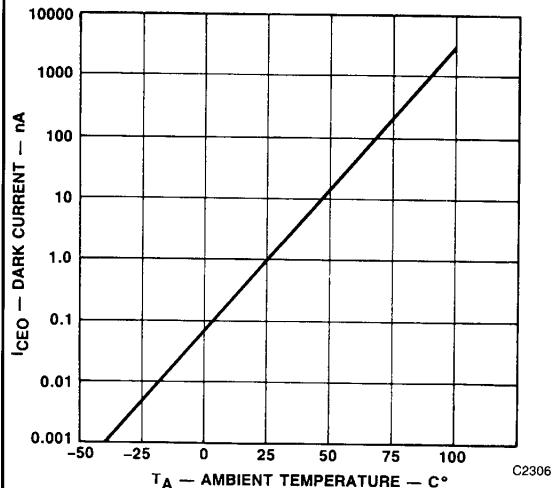


Fig. 5 Dark Current vs.
Temperature

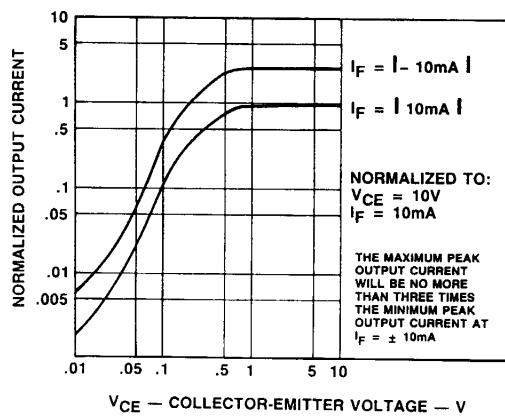


Fig. 6. Output Symmetry Characteristics

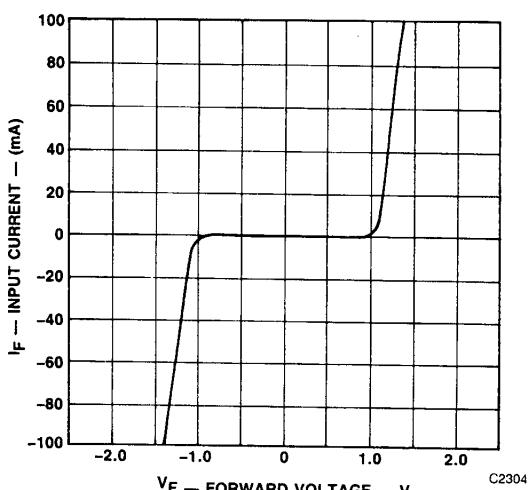


Fig. 7.



AC INPUT/PHOTOTRANSISTOR OPTOCOUPLES

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.